

Silicon PNP Power Transistors

2SB1149

DESCRIPTION

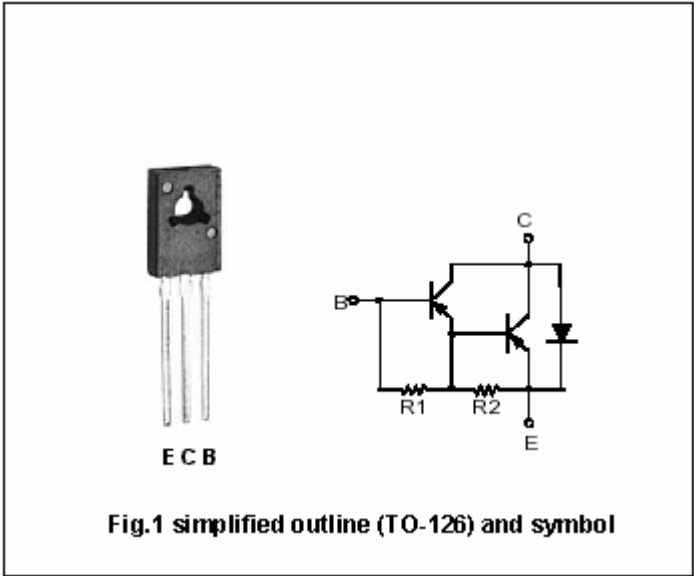
- With TO-126 package
- DARLINGTON
- High DC current gain
- Low collector saturation voltage

APPLICATIONS

- For use in operating from IC without predriver ,such as hammer driver

PINNING(See Fig.2)

PIN	DESCRIPTION
1	Emitter
2	Collector;connected to mounting base
3	Base



Absolute maximum ratings(Ta=25)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	-100	V
V_{CEO}	Collector-emitter voltage	Open base	-100	V
V_{EBO}	Emitter-base voltage	Open collector	-8	V
I_C	Collector current (DC)		-3.0	A
I_{CM}	Collector current-peak		-5.0	A
P_D	Total power dissipation	$T_a=25$	1.3	W
		$T_c=25$	15	
T_j	Junction temperature		150	
T_{stg}	Storage temperature		-55~150	

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CHARACTERISTICS

T_j=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CEsat}	Collector-emitter saturation voltage	I _C =-1.5A ; I _B =-1.5mA		-0.9	-1.2	V
V _{BEsat}	Base-emitter saturation voltage	I _C =-1.5A ; I _B =-1.5mA		-1.5	-2.0	V
I _{CBO}	Collector cut-off current	V _{CB} =-100V; I _E =0			-10	μ A
I _{EBO}	Emitter cut-off current	V _{EB} =-5V; I _C =0			-2.0	mA
h _{FE-1}	DC current gain	I _C =-1.5A ; V _{CE} =-2V	2000		15000	
h _{FE-2}	DC current gain	I _C =-3A ; V _{CE} =-2V	1000			

Switching times

t _{on}	Turn-on time	I _C =-1.5A ; I _{B1} =-I _{B2} =-1.5mA V _{CC} ≈ -40V; R _L =27 Ω		0.5		μ s
t _{stg}	Storage time			2.0		μ s
t _f	Fall time			1.0		μ s

◆ h_{FE-1} Classifications

M	L	K
2000-5000	3000-7000	5000-15000

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PACKAGE OUTLINE

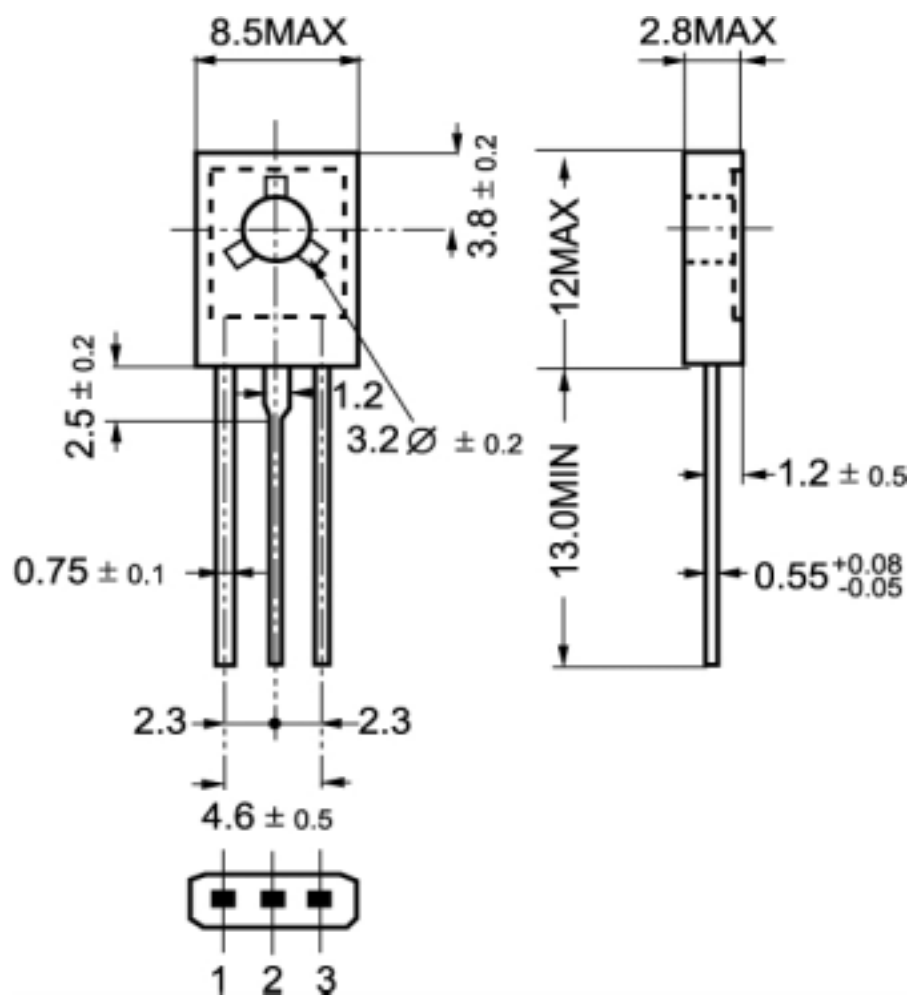


Fig.2 Outline dimensions